

Fig. 1: SIMS profiles of phosphorus in silicon after two different flash anneals with 135 J/cm² on samples with ALD PO_x/SiO_x dopant source layer capped with Sb₂O₅.

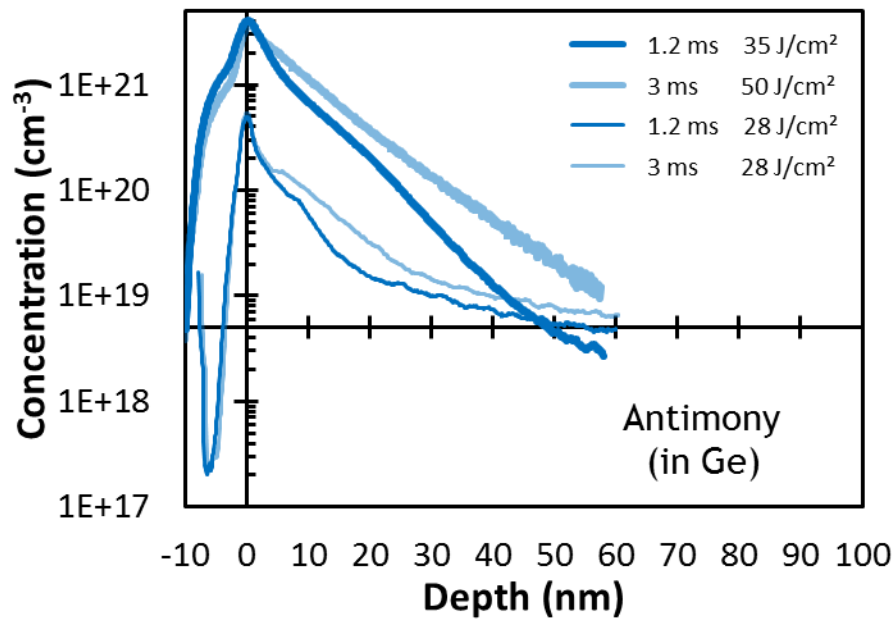


Fig. 2: SIMS profiles of antimony in germanium after four different flash anneals on samples with ALD Sb₂O₅ films.